- State-of-the-Art Advanced BiCMOS Technology (ABT) Widebus™ Design for 2.5-V and 3.3-V Operation and Low Static **Power Dissipation**
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 2.3-V to 3.6-V V_{CC})
- Typical V_{OLP} (Output Ground Bounce) $< 0.8 \text{ V at V}_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- High Drive (-24/24 mA at 2.5-V and -32/64 mA at 3.3-V V_{CC})
- **Power Off Disables Outputs, Permitting Live Insertion**
- **High-Impedance State During Power Up** and Power Down Prevents Driver Conflict
- Uses Bus Hold on Data Inputs in Place of **External Pullup/Pulldown Resistors to** Prevent the Bus From Floating
- **Auto3-State Eliminates Bus Current** Loading When Output Exceeds V_{CC} + 0.5 V
- Latch-Up Performance Exceeds 250 mA Per **JESD 17**
- **ESD Protection Exceeds 2000 V Per** MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model; and Exceeds 1000 V **Using Charged-Device Model, Robotic** Method
- Flow-Through Architecture Facilitates **Printed Circuit Board Layout**
- Distributed V_{CC} and GND Pin Configuration **Minimizes High-Speed Switching Noise**
- **Package Options Include Plastic Shrink** Small-Outline (DL), Thin Shrink Small-Outline (DGG), Thin Very Small-Outline (DGV) Packages, and 380-mil Fine-Pitch Ceramic Flat (WD) Package

SN54ALVTH16827 . . . WD PACKAGE SN74ALVTH16827...DGG, DGV, OR DL PACKAGE (TOP VIEW)

		П		1	
10E1	1	\cup	56	þ	10E2
1Y1[2		55	1	1A1
1Y2[3		54	1	1A2
GND[4		53	1	GND
1Y3[5		52	1	1A3
1Y4[6		51	1	1A4
V _{CC} [7		50	1	V_{CC}
1Y5[8		49	1	1A5
1Y6[9		48	1	1A6
1Y7[10		47	þ	1A7
GND[11		46	þ	GND
1Y8[12		45	þ	1A8
1Y9[13		44	1	1A9
1Y10[14		43	1	1A10
2Y1[15		42	1	2A1
2Y2[16		41	1	2A2
2Y3[17		40	1	2A3
GND[18		39	1	GND
2Y4[19		38	0	2A4
2Y5[20		37	1	2A5
2Y6[21		36	P	2A6
v _{cc} [22		35	P	V_{CC}
2Y7[23		34	1	2A7
2Y8[24		33	0	2A8
GND[25		32	0	GND
2Y9[26		31	1	2A9
2Y10	27		30	6	2 <u>A10</u>
2OE1	28		29	P	2OE2

description

The 'ALVTH16827 devices are 20-bit buffers/line drivers designed for 2.5-V or 3.3-V V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The devices are composed of two 10-bit sections with separate output-enable signals. For either 10-bit buffer section, the two output-enable ($1\overline{OE1}$ and $1\overline{OE2}$, or $2\overline{OE1}$ and $2\overline{OE2}$) inputs must be low for the corresponding Y outputs to be active. If either output-enable input is high, the outputs of that 10-bit buffer section are in the high-impedance state.



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SN54ALVTH16827, SN74ALVTH16827 2.5-V/3.3-V 20-BIT BUFFERS/DRIVERS WITH 3-STATE OUTPUTS

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description (continued)

When V_{CC} is between 0 and 1.2 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.2 V, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

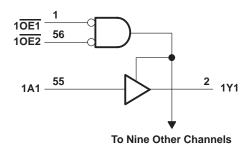
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

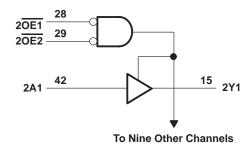
The SN54ALVTH16827 is characterized for operation over the full military temperature range of -55°C to 125°C. The SN74ALVTH16827 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE (each 10-bit section)

	OUTPUT		
OE1	OE2	Α	Y
L	L	L	L
L	L	Н	Н
Н	X	Χ	Z
Х	Н	Χ	Z

logic diagram (positive logic)





absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage range, V _{CC}	. -0.5 V to 4.6 V
Input voltage range, V _I (see Note 1)	-0.5 V to 7 V
Voltage range applied to any output in the high-impedance	
or power-off state, V _O (see Note 1)	-0.5 V to 7 V
Voltage range applied to any output in the high state, V _O (see Note 1)	-0.5 V to 7 V
Output current in the low state, I _O : SN54ALVTH16827	96 mA
SN74ALVTH16827	128 mA
Output current in the high state, IO: SN54ALVTH16827	–48 mA
SN74ALVTH16827	–64 mA
Input clamp current, I _{IK} (V _I < 0)	–50 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Package thermal impedance, θ _{JA} (see Note 2): DGG package	81°C/W
DGV package	86°C/W
DL package	74°C/W
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 - 2. The package thermal impedance is calculated in accordance with JESD 51.



recommended operating conditions, $V_{\mbox{\footnotesize{CC}}}$ = 2.5 V \pm 0.2 V (see Note 3)

			SN54ALVTH16827			SN74ALVTH16827			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	UNII
Vcc	Supply voltage		2.3		2.7	2.3		2.7	V
VIH	High-level input voltage		1.7			1.7			V
V _{IL}	Low-level input voltage			Ĺ	0.7			0.7	V
VI	Input voltage		0	Vcc	5.5	0	VCC	5.5	V
IOH	High-level output current			,0	-6			-8	mA
la	Low-level output current			\C)	6			8	mA
lor	Low-level output current; current duty cycle ≤	50%; f ≥ 1 kHz	5	2	18			24	IIIA
Δt/Δν	Input transition rise or fall rate	Outputs enabled	40		10			10	ns/V
Δt/ΔV _{CC}	Power-up ramp rate		200			200			μs/V
TA	Operating free-air temperature		-55		125	-40		85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

recommended operating conditions, $V_{\mbox{\footnotesize{CC}}}$ = 3.3 V \pm 0.3 V (see Note 3)

			SN54	ALVTH1	6827	SN74ALVTH16827			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	UNII
Vcc	Supply voltage		3		3.6	3		3.6	V
VIH	High-level input voltage		2			2			V
V _{IL}	Low-level input voltage				0.8			0.8	V
VI	Input voltage		0	VCC	5.5	0	Vcc	5.5	V
ЮН	High-level output current			,Q	-24			-32	mA
lai	Low-level output current			Ó	24			32	mA
lor	Low-level output current; current duty cycle ≤	50%; f≥1 kHz	0	2	48			64	IIIA
Δt/Δν	Input transition rise or fall rate	Outputs enabled	20		10			10	ns/V
Δt/ΔV _{CC}	Power-up ramp rate		200			200			μs/V
T _A	Operating free-air temperature		-55		125	-40		85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

SN54ALVTH16827, SN74ALVTH16827 2.5-V/3.3-V 20-BIT BUFFERS/DRIVERS WITH 3-STATE OUTPUTS

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electrical characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V \pm 0.2 V (unless otherwise noted)

PARAMETER		TEST OF	ONDITIONS	SN54	ALVTH1	6827	SN74	ALVTH1	6827	UNIT
		lESI CC	ONDITIONS	MIN	TYP [†]	MAX	MIN	TYP†	MAX	UNII
VIK		$V_{CC} = 2.3 \text{ V},$	I _I = -18 mA			-1.2			-1.2	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V},$	$I_{OH} = -100 \mu A$	V _{CC} -0.	2		V _{CC} -0	.2		
Voн		V _{CC} = 2.3 V	$I_{OH} = -6 \text{ mA}$	1.8						V
		vCC = 2.3 v	$I_{OH} = -8 \text{ mA}$				1.8			
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V},$	$I_{OL} = 100 \mu\text{A}$			0.2			0.2	
			$I_{OL} = 6 \text{ mA}$			0.4			0.47	
VOL		V _{CC} = 2.3 V	$I_{OL} = 8 \text{ mA}$						0.4	V
Control inputs	VCC = 2.3 V	$I_{OL} = 18 \text{ mA}$			0.5					
		$I_{OL} = 24 \text{ mA}$						0.5		
Control inputs	$V_{CC} = 2.7 \text{ V},$	$V_I = V_{CC}$ or GND			±1			±1		
	Control inputs	$V_{CC} = 0 \text{ or } 2.7 \text{ V},$	V _I = 5.5 V			10			10	
IJ	1	s V _{CC} = 2.7 V	V _I = 5.5 V			3 10			10	μΑ
	Data inputs		AI = ACC	<u> </u>			1			
			V _I = 0		Q ²	- 5			- 5	
l _{off}		$V_{CC} = 0$,	V_I or $V_O = 0$ to 4.5 V		5				±100	μΑ
I _{BHL} ‡		$V_{CC} = 2.3 \text{ V},$	V _I = 0.7 V	\perp	115			115		μΑ
IBHH§		$V_{CC} = 2.3 \text{ V},$	V _I = 1.7 V	0	-10			-10		μΑ
I _{BHLO}		$V_{CC} = 2.7 \text{ V},$	$V_I = 0$ to V_{CC}	300			300			μΑ
Івнно	#	$V_{CC} = 2.7 \text{ V},$	$V_I = 0$ to V_{CC}	-300			-300			μΑ
{IEX}		$V{CC} = 2.3 \text{ V},$	V _O = 5.5 V			125			125	μΑ
IOZ(PL	J/PD)☆	$V_{CC} \le 1.2 \text{ V}, V_{O} = \frac{0.5}{OE} \text{ V}$ V _I = GND or V _{CC} , \overline{OE} =	to V _{CC} , don't care			±100			±100	μΑ
IOZH		V _{CC} = 2.7 V	$V_O = 2.3 \text{ V},$ $V_I = 0.7 \text{ V or } 1.7 \text{ V}$			5			5	μΑ
l _{OZL}		V _{CC} = 2.7 V	V _O = 0.5 V, V _I = 0.7 V or 1.7 V			-5			-5	μΑ
		V _{CC} = 2.7 V,	Outputs high		0.04	0.1		0.04	0.1	
ICC		$I_{O} = 0$,	Outputs low		2.3	5		2.3	5	mA
		$V_I = V_{CC}$ or GND	Outputs disabled		0.04	0.1		0.04	0.1	
C _i		$V_{CC} = 2.5 \text{ V},$	$V_1 = 2.5 \text{ V or } 0$		3			3		pF
Co		V _{CC} = 2.5 V,	V _O = 2.5 V or 0		6			6		pF

[†] All typical values are at $V_{CC} = 2.5 \text{ V}$, $T_A = 25^{\circ}\text{C}$.



[‡]The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IL} max.

[§] The bus-hold circuit can source at least the minimum high sustaining current at VIH min. IBHH should be measured after raising VIN to VCC and then lowering it to VIH min.

[¶] An external driver must source at least IBHLO to switch this node from low to high.

[#] An external driver must sink at least IBHHO to switch this node from high to low.

Current into an output in the high state when VO > VCC

[★]High-impedance state during power up or power down

electrical characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V \pm 0.3 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54	SN54ALVTH16827			SN74ALVTH16827		
Ρ/	ARAWETER	1531 (CONDITIONS	MIN	TYP†	MAX	MIN	TYP†	MAX	UNIT
٧ıK		V _{CC} = 3 V,	I _I = -18 mA			-1.2			-1.2	V
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V},$	I _{OH} = -100 μA	V _{CC} -0	.2		V _{CC} -0.2			
V _{OH}		VCC = 3 V	$I_{OH} = -24 \text{ mA}$	2						V
		ACC = 2 A	$I_{OH} = -32 \text{ mA}$				MIN TYPT MAX -1.2 V _{CC} -0.2 2 0.2 0.4 0.5 0.55 110 10 10 11 -5 +100 75 -75 500 -500 125 ±100 5 0.07 0.1 3.2 6 0.07 0.1			
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V},$	I _{OL} = 100 μA			0.2			0.2	
			I _{OL} = 16 mA						0.4	
\/a.			$I_{OL} = 24 \text{ mA}$			0.5				V
VOL		V _{CC} = 3 V	$I_{OL} = 32 \text{ mA}$						0.5	V
			$I_{OL} = 48 \text{ mA}$			0.55				
		$I_{OL} = 64 \text{ mA}$						0.55		
	Control inputs	$V_{CC} = 3.6 \text{ V},$	$V_I = V_{CC}$ or GND			±1			±1	
	Control inputs	$V_{CC} = 0 \text{ or } 3.6 \text{ V},$	V _I = 5.5 V			10			10	
lį		Data inputs V _{CC} = 3.6 V	V _I = 5.5 V			10			10	μΑ
	Data inputs		VI = VCC		, i	1			1	
			V _I = 0		O. C.	- 5			– 5	
l _{off}		$V_{CC} = 0$,	V_I or $V_O = 0$ to 4.5 V		C				±100	μΑ
I _{BHL} ‡		V _{CC} = 3 V,	V _I = 0.8 V	75	20		75			μΑ
I _{BHH} §	}	V _{CC} = 3 V,	V _I = 2 V	-75	,		-75			μΑ
IBHLO	,¶	$V_{CC} = 3.6 \text{ V},$	$V_I = 0$ to V_{CC}	500			500			μΑ
Івнно) [#]	$V_{CC} = 3.6 \text{ V},$	$V_I = 0$ to V_{CC}	-500			-500			μΑ
ΙΕΧ		$V_{CC} = 3 V$,	$V_0 = 5.5 \text{ V}$			125			125	μΑ
I _{OZ(PI}	U/PD) [☆]	$V_{CC} \le 1.2 \text{ V}, V_{O} = \frac{0.5}{\text{OE}}$ $V_{I} = \text{GND or } V_{CC}, \overline{\text{OE}}$	V to V _{CC} , = don't care			±100			±100	μΑ
lozh		V _{CC} = 3.6 V	V _O = 3 V, V _I = 0.8 V or 2 V			5			5	μΑ
l _{OZL}		V _{CC} = 3.6 V	$V_O = 0.5 \text{ V},$ $V_I = 0.8 \text{ V or 2 V}$			- 5			-5	μΑ
		V _{CC} = 3.6 V,	Outputs high		0.07	0.1		0.07	0.1	
ICC		$I_{O} = 0$,	Outputs low		3.2	6		3.2	6	mA
		$V_I = V_{CC}$ or GND	Outputs disabled		0.07	0.1		0.07	0.1	
∆lcc□	1	V _{CC} = 3 V to 3.6 V, Or Other inputs at V _{CC} or	ne input at V _{CC} – 0.6 V, GND			0.4			0.4	mA
Ci		V _{CC} = 3.3 V,	V _I = 3.3 V or 0		3			3		pF
Со		V _{CC} = 3.3 V,	V _O = 3.3 V or 0	1	6			6		pF

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.



[‡] The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IL} max.

[§] The bus-hold circuit can source at least the minimum high sustaining current at VIH min. IBHH should be measured after raising VIN to VCC and then lowering it to VIH min.

[¶] An external driver must source at least IBHLO to switch this node from low to high.

[#] An external driver must sink at least I_{BHHO} to switch this node from high to low.

 $[\]parallel$ Current into an output in the high state when $\vee_{O} > \vee_{CC}$

[★]High-impedance state during power up or power down

 $[\]Box$ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

SN54ALVTH16827, SN74ALVTH16827 2.5-V/3.3-V 20-BIT BUFFERS/DRIVERS WITH 3-STATE OUTPUTS

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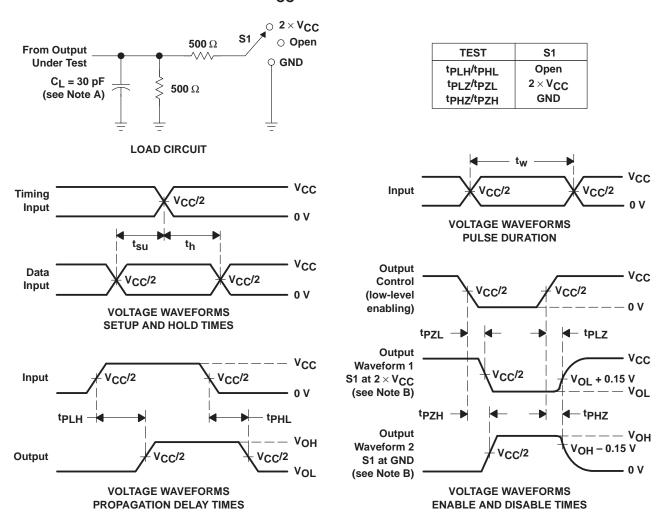
switching characteristics over recommended operating free-air temperature range, C_L = 30 pF, V_{CC} = 2.5 V \pm 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	то	SN54ALVTI	116827	SN74ALVT	H16827	UNIT
PARAMETER	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	UNIT
^t PLH	۸	V	1.5	3.2	1.5	3.2	ns
^t PHL	Α	'	1.7	3.7	1.7	3.7	115
^t PZH	<u> </u>	V	1.9	4.3	1.9	4.3	ns
^t PZL	ŌĒ	T I	1.8	4	1.8	4	115
^t PHZ	ŌĒ	V	2.5	5.6	2.5	5.6	ns
t _{PLZ}	OE	·	1.7	4.6	1.7	4.6	115

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF, V_{CC} = 3.3 V \pm 0.3 V (unless otherwise noted) (see Figure 2)

PARAMETER	FROM	то	TO SN54ALVTH16827 SN7				UNIT
	(INPUT)	(OUTPUT)	MIN	MIN	MAX	UNIT	
tPLH	۸	V	1.8	3	1.8	3	ns
^t PHL	A	T	1.6	2.8	1.6	2.8	115
^t PZH	ŌĒ	V	1.6	3.9	1.6	3.9	ns
^t PZL	OE	Ť	1.5	3.4	1.5	3.4	115
^t PHZ	ŌĒ	V	3.3	5.8	3.3	5.8	ns
t _{PLZ}	OE .	ľ	2.6	4.6	2.6	4.6	113

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$

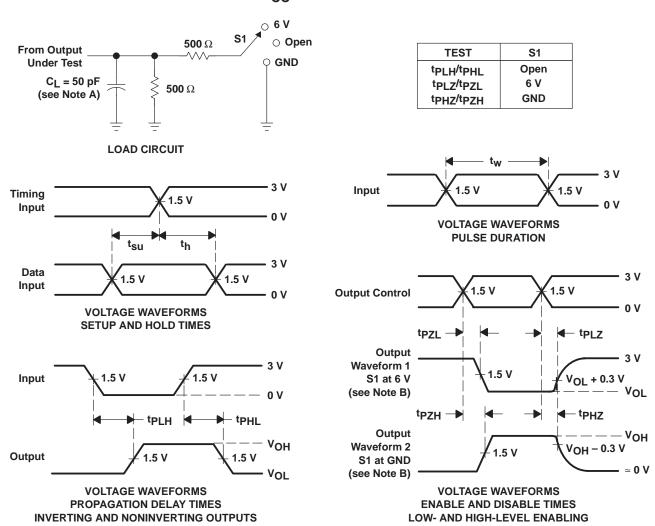


NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq 2$ ns. $t_f \leq 2$ ns.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$



- NOTES: A. C_I includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform22 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \,\Omega$, $t_f \leq 2.5 \,\text{ns}$, $t_f \leq 2.5 \,\text{ns}$.
 - D. The outputs are measured one at a time with one transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms



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